

S(A)S-255A

Schottky barrier diode with tre... OS structure

Item	Item	Information
	Die Size (A)	2... 94 mil
	Top Metal Pad Size (B)	2... 90mil
	Chip Size (C)	2... 91mil
	Wafer Thickness (D)	2... 9.5 mil
	Scribe Line Width (E)	3.15 mil
	Wafer Size	6 inch
	Top Side Metallization	AL/Ag
Back Side Metallization	Ni Ag	
Recommended Storage Environment	Store in original container, in dry n... (6 months at an ambi... erature of 23	

Characteristics (T_J=25

Description	Min.	Typ.	Max.	Test Condition
Breakdown Voltage	155	170	-	I _R = 100μA
Forward Voltage	-	0.8	0.8	I _F = 10A ⁽³⁾
Forward Current	-	0.5	10	V _R = 150V
Operating Storage Temperature	-40	to 150	Max	